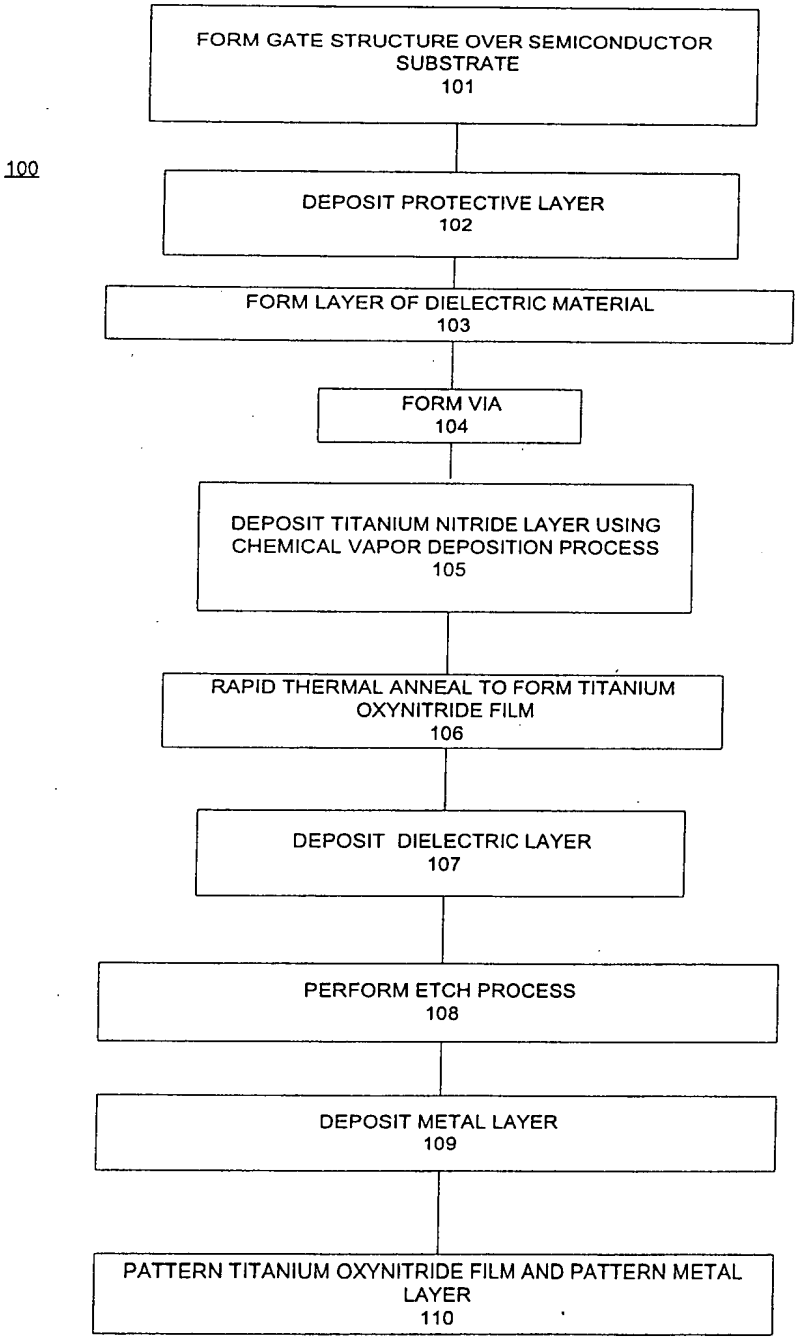

100
FORM GATE STRUCTURE OVER SEMICONDUCTOR SUBSTRATE
101
DEPOSIT PROTECTIVE LAYER
102
FORM LAYER OF DIELECTRIC MATERIAL
103
FORM VIA
104
DEPOSIT TITANIUM NITRIDE LAYER USING CHEMICAL VAPOR DEPOSITION PROCESS
105
RAPID THERMAL ANNEAL TO FORM TITANIUM OXYNITRIDE FILM
106
DEPOSIT DIELECTRIC LAYER
107
PERFORM ETCH PROCESS
108
DEPOSIT METAL LAYER
109
PATTERN TITANIUM OXYNITRIDE FILM AND PATTERN METAL LAYER
110

FIG. 1

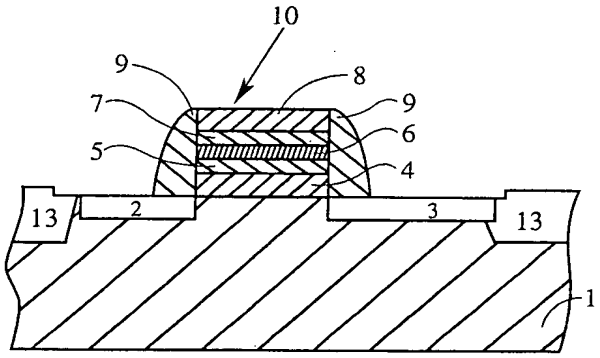



FIG. 2

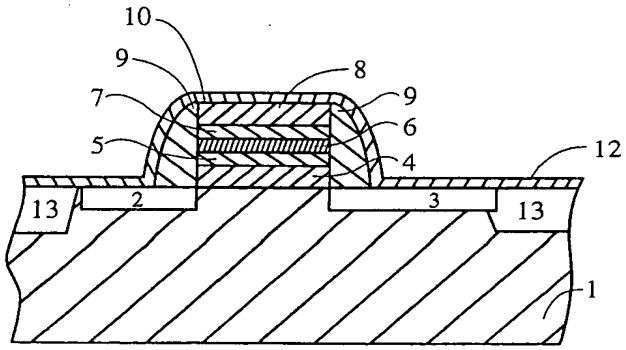



FIG. 3

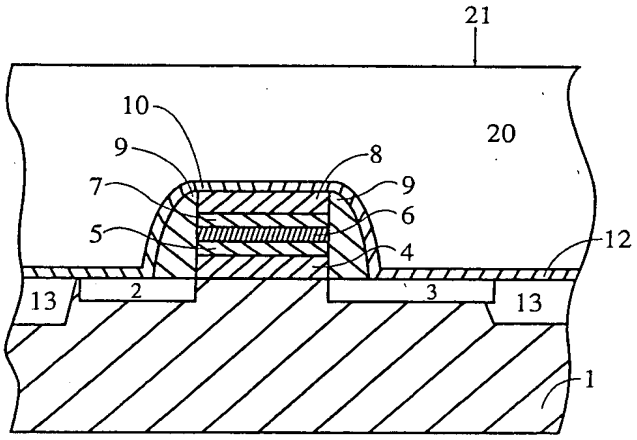



FIG. 4

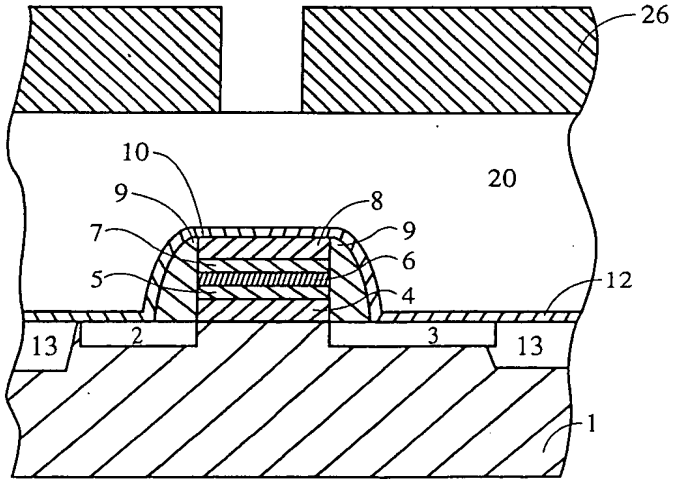



FIG. 5

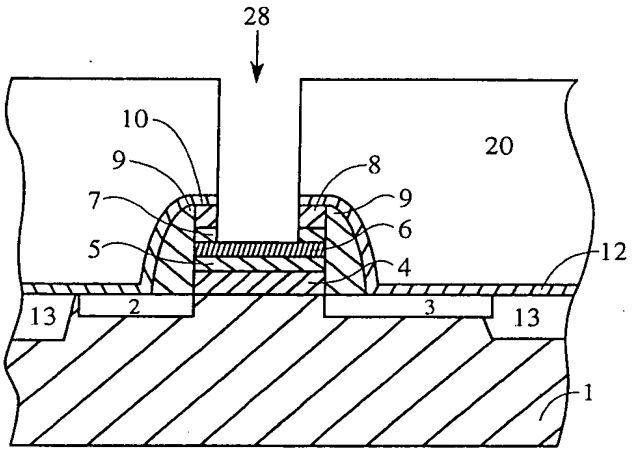



FIG. 6

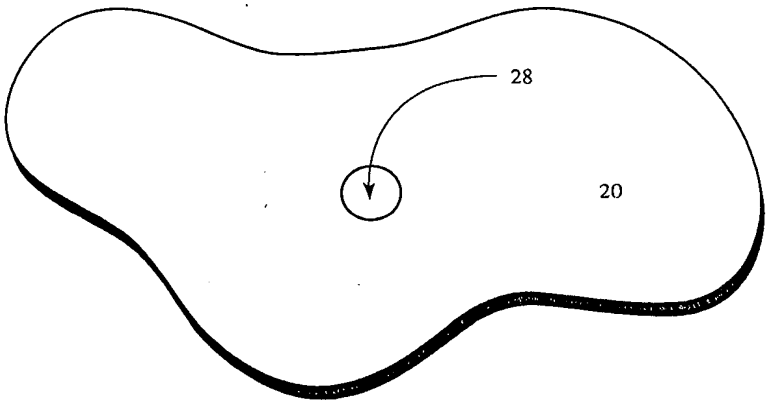



FIG. 7

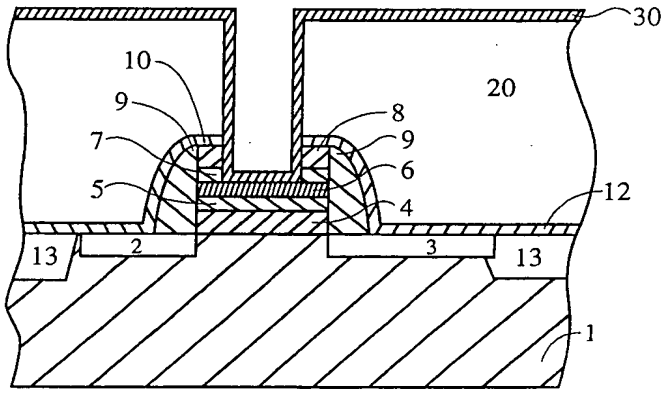



FIG. 8

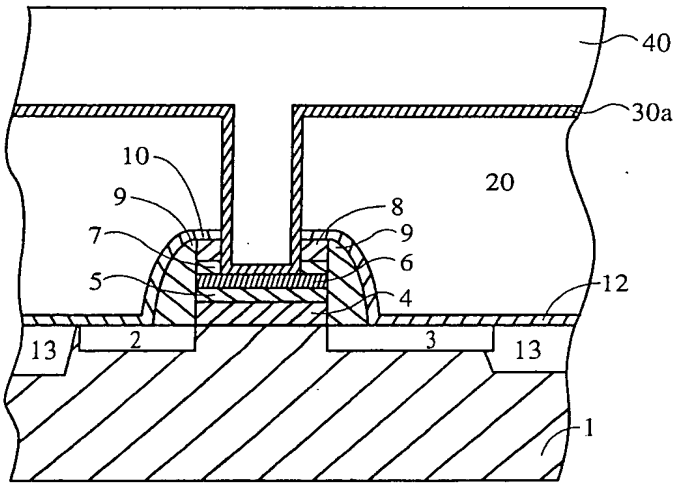



FIG. 9

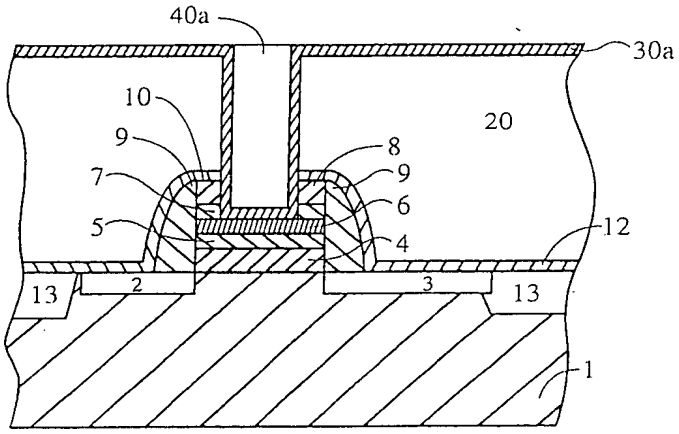

40a
30a
10
20
9
8
7
9
6
5
4
12
13
2
3
13
1

FIG. 10

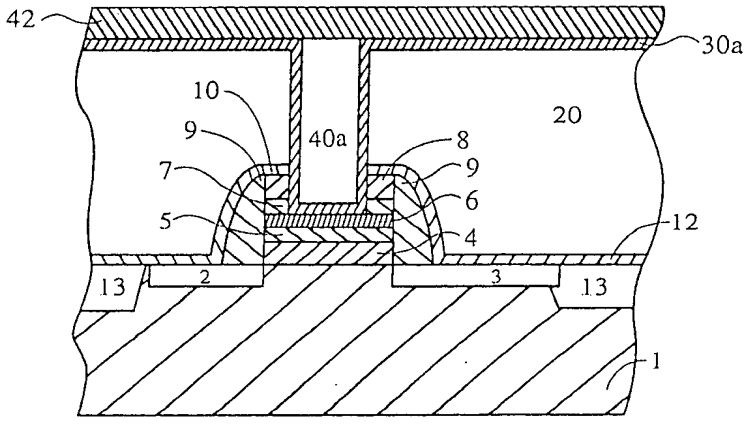

42
30a
10
20
9
40a
8
7
9
6
5
4
12
13
2
3
13
1

FIG. 11

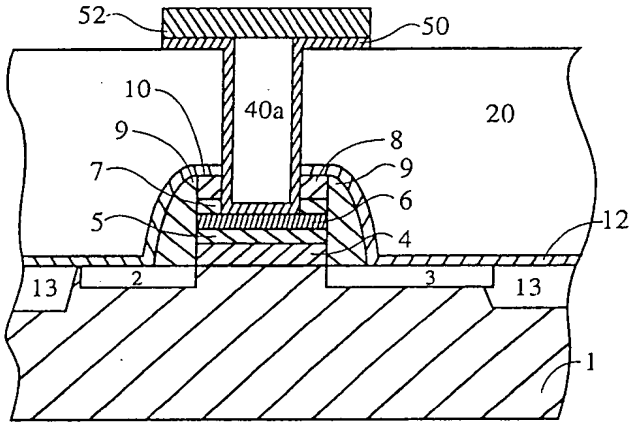



FIG. 12

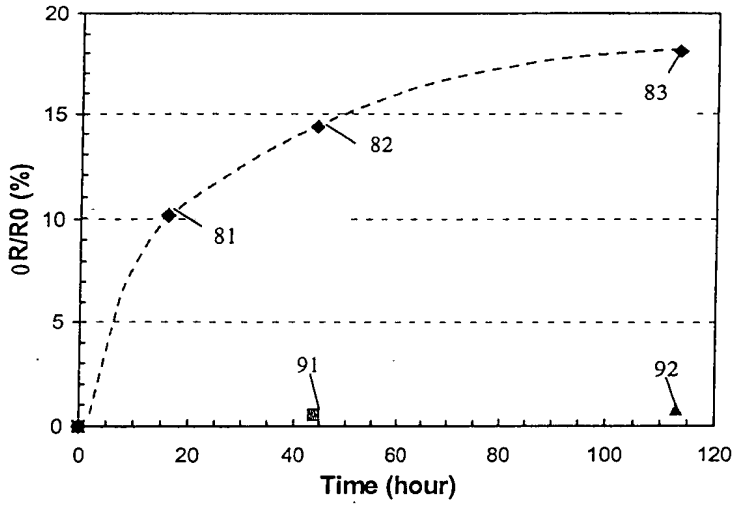



Fig. 13